

MiniSKiiP® 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 35NAB12T4V1

Features

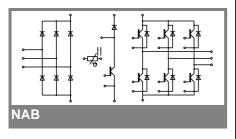
- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 26 kVA
- Typical motor power 15 kW

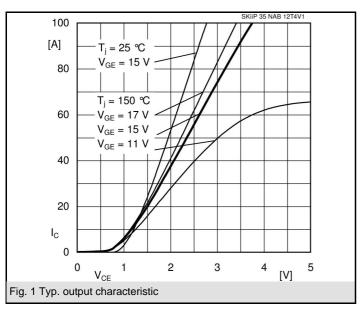
Remarks

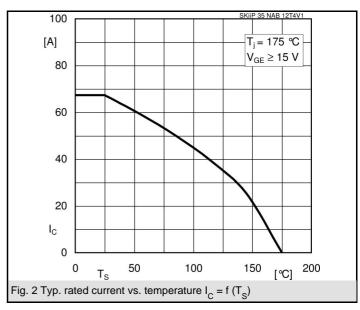
- V_{CEsat} , V_{F} = chip level value Case temp. limited to T_{C} = 125°C max. (for baseplateless modules $T_C = T_S$
- product rel. results valid for $T_i \le 150$ (recomm. $T_{op} = -40$... +150°C)

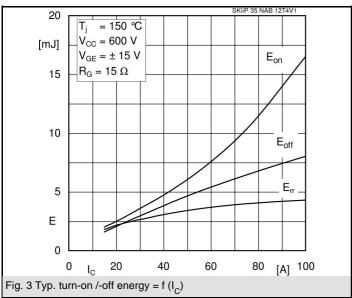


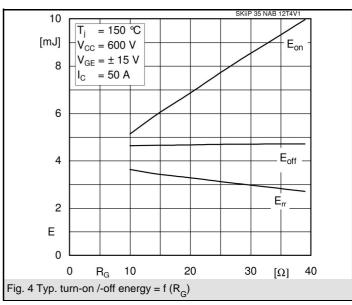
Absolute Maximum Ratings $T_s = 25$ °C, unless otherwise specifie							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		1200	V				
I _C	T _s = 25 (70) °C	67 (52)	Α				
I _{CRM}		150	Α				
V_{GES}		± 20	V				
T _j		- 40 + 175	°C				
Diode - Inverter, Chopper							
I _F	$T_s = 25 (70) ^{\circ}C$	60 (48)	Α				
I _{FRM}		150	Α				
T _j		- 40 + 175	°C				
Diode - Rectifier							
V_{RRM}		1600	V				
I _F	T _s = 70 °C	61	Α				
I _{FSM}	$t_{\rm p}$ = 10 ms, sin 180 °, $T_{\rm i}$ = 25 °C	700	Α				
i²t	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_i = 25 ^\circ\text{C}$	2400	A²s				
T _j		- 40 + 150	°C				
Module							
I _{tRMS}	per power terminal (20 A / spring)	80	Α				
T _{stg}		- 40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

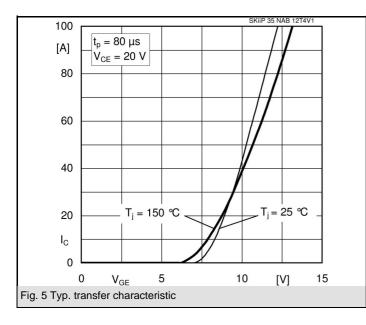
Character	ristics	T _s = 25 °C	s = 25 °C, unless otherwise specified					
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V _{CEsat} V _{GE(th)} V _{CE(TO)} r _T C _{ies}	$\begin{split} & I_{\text{Cnom}} = 50 \text{ A, } T_j = 25 \text{ (150) °C} \\ &V_{\text{GE}} = V_{\text{CE}}, I_{\text{C}} = 2 \text{ mA} \\ &T_j = 25 \text{ (150) °C} \\ &T_j = 25 \text{ (150) °C} \\ &V_{\text{CE}} = 25 \text{ V, } V_{\text{GE}} = 0 \text{ V, } f = 1 \text{ MHz} \\ &V_{\text{CE}} = 25 \text{ V, } V_{\text{GE}} = 0 \text{ V, } f = 1 \text{ MHz} \end{split}$	5	1,85 (2,25) 5,8 0,8 (0,7) 21 (31) 2,77 0,21	2,05 (2,45) 6,5 0,9 (0,8) 23 (33)	V V WΩ nF nF			
C _{oes} C _{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,16		nF			
R _{th(j-s)}	per IGBT		0,71		K/W			
$\begin{aligned} & t_{d(on)} \\ & t_r \\ & t_{d(off)} \\ & t_f \\ & E_{on} \\ & E_{off} \end{aligned}$	under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_{Cnom} = 50 \text{ A}, T_j = 150^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 15 \Omega$ inductive load verter, Chopper $I_{Fnom} = 50 \text{ A}, T_j = 25 (150)^{\circ}\text{C}$ $T_j = 25 (150)^{\circ}\text{C}$		60 35 370 60 6 4,7 2,25 (2,2) 1,3 (0,9) 19 (26)	2,55 (2,5) 1,5 (1,1) 21 (28)	ns ns ns ns mJ mJ			
$R_{th(j-s)}$	per diode		0,95		K/W			
I _{RRM} Q _{rr} E _{rr}	under following conditions $I_{Fnom} = 50 \text{ A}, V_R = 600 \text{ V}$ $V_{GE} = 0 \text{ V}, T_j = 150 \text{ °C}$ $di_F/dt = 1400 \text{ A/µs}$		45 8,6 3,4		Α μC mJ			
Diode - Rectifier								
$V_{\text{F}} \\ V_{\text{(TO)}} \\ r_{\text{T}} \\ R_{\text{th(j-s)}}$	$I_{Fnom} = 35 \text{ A}, T_j = 25 \text{ °C}$ $T_j = 150 \text{ °C}$ $T_j = 150 \text{ °C}$ per diode		1,1 0,8 11 0,9		V V mΩ K/W			
Temperature Sensor								
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω			
Mechanical Data								
w M _s	Mounting torque	2	95	2,5	g Nm			

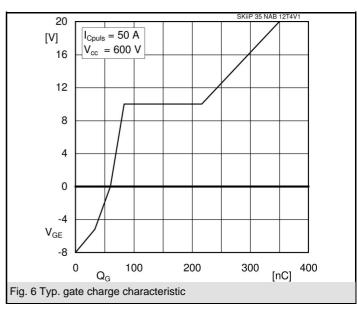


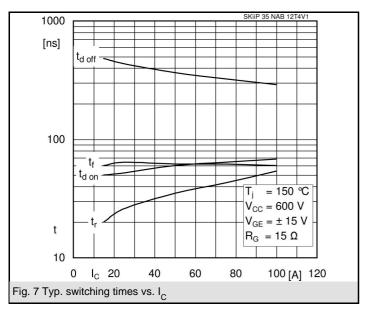


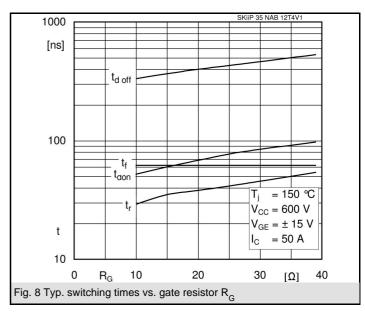


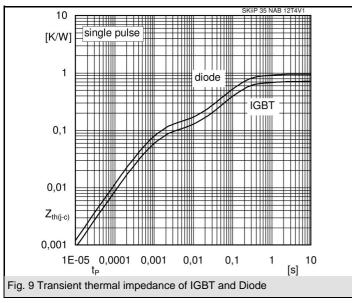


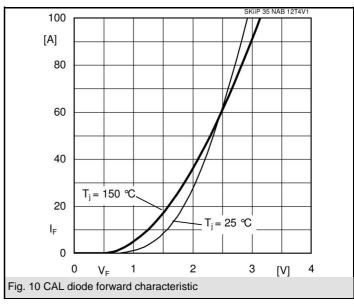


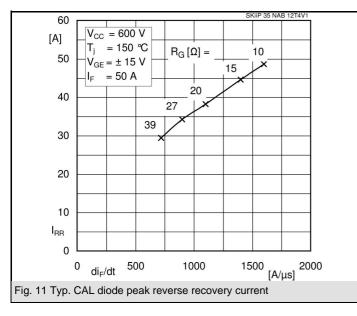


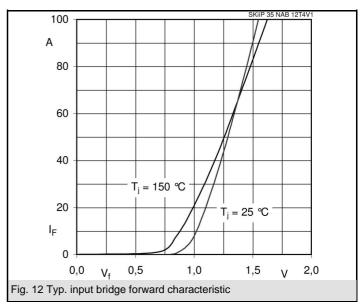


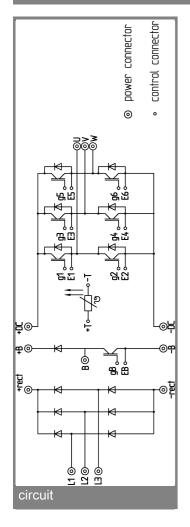


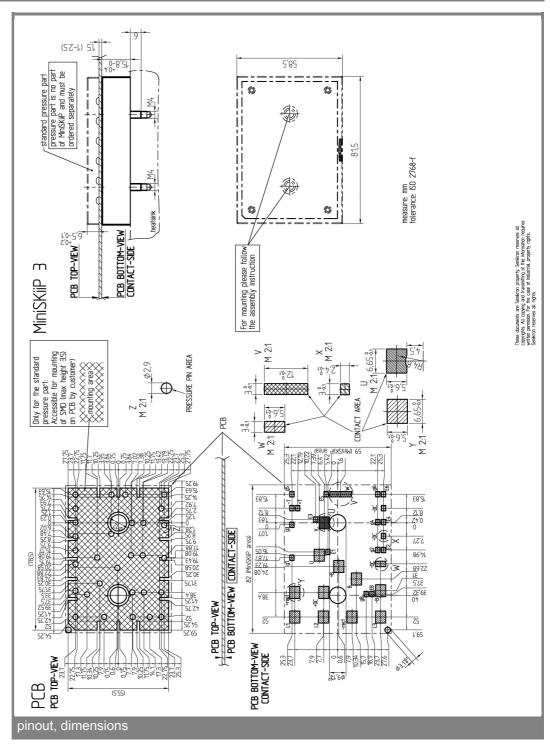












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.